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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

	SHEET 1 OF 1
ATTORNEY'S DKT No.	APPLICATION NO.
015290-517	09/788,365
APPLICANT	
Tuqiang NI et al.	
FILING DATE	GROUP
February 21, 2001	1763

JUN 1 1 2001 U.S. PATENT DOCUMENTS A TROS Patent Document Name of Patentee or Applicant Sc Date of Publication Kind Code Examiner Initials Number (if known) of Cited Document (MM-DD-YYYY) 4,270,999 Hassan et al. 345.33 06/02/81 4,614,639 09/30/86 156 Hegedus 723E 09/08/87 4,691,662 Roppel et al. 118 4,943,345 Asmussen et al. 07/24/90 4,992,301 Shishiguchi et al. 02/12/91 02/26/91 4,996,077 Moslehi et al. 5,134,965 Tokuda et al. 08/04/92 5,164,040 Eres et al. 11/17/92 10/12/93 5,252,133 Miyazaki et al. 06/04/96 Suzuki et al. 5,522,934 06/11/96 5,525,159 Hama et al. Ishii 06/25/96 5,529,657 07/02/96 5,531,834 Ishizuka et al. Quian 07/30/96 5,540,800 12/03/96 Paranipe et al. 5,580,385 *+2.*2MD 118 5,614,055 Fairbairn et al. 03/25/97 FOREIGN PATENT DOCUMENTS Foreign Patent Document Examiner Kind Code **Date of Publication** Translation (MM-DD-YXYY) Initials Number (if known) Country Yes no NON PATENT LITERATURE DOCUMENTS Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), Examiner publisher, city and/or country where published. Initials "Electron Cyclotron Resonance Microwave Discharges for Etching and Thin-film Deposition," J. Vacuum Science and Technology A, Vol. 7, pp. 883-893 (1989) by J. ASMUSSEN; "Low-temperature Deposition of Silicon Dioxide Films from Electron Cyclotron Resonant Microwave Plasmas," J. Applied Physics, Vol. 65, pp. 2457-2463 (1989) by T.V. HERAK et al., "New Approach to Low Temperature Deposition of High-quality Thin Films by Electron Cyclotron Resonance Microwave Plasmas, "J. Vac. Sci. Tech, B, Vol. 10, pp. 2170-2178 (1992) by T.T. CHAU et al.; Examiner Date

Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

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